# ECN3053F Application Note

## 1. Introduction

ECN3053F is a high-voltage driver IC that can drive 3-phase MOS-gated devices to which converted AC200~230V power supplies are applied. The use of six external IGBTs or MOSFETs allows 3-phase induction motors and DC brushless motors to be controlled at variable speed. Fig. 1 shows a basic block diagram of a typical ECN3053F system.

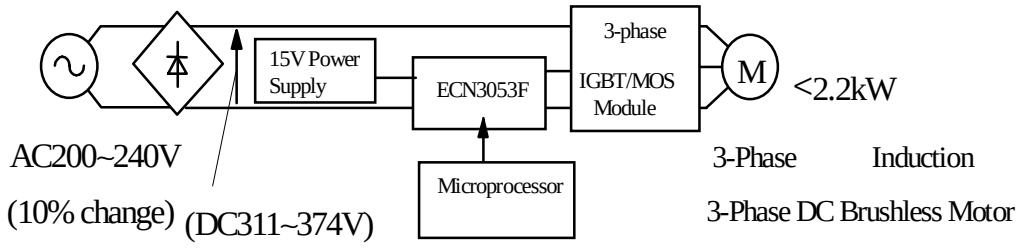



Fig. 1 Configuration of a variable-speed control system with 3-phase motors

ECN3053F can drive up to 30A IGBTs or MOSFETs, and control the speed of 3-phase motors with an output of up to 2.2kW at variable speed. The applicable motor output of a 3-phase induction motor can generally be determined by the following equation,

$$\text{Motor output} = 1.73 \times Vs \times I_M \times \cos\phi \times \eta$$

Vs:DC voltage, $I_M$:Motor current, $\cos\phi$:Power factor≈0.8,

$\eta$:Motor efficiency≈0.8

## 2. Driving by a floating power supply and by a bootstrap system

Each phase has two external IGBTs which have a totem pole configuration. In order to turn on IGBTs, the gate voltage needs to be higher than the threshold voltage Vth(about 5V) against the source voltage. The source of bottom arm IGBTs is fixed to the ground voltage. Therefore, they can be driven by applying Vcc voltage to the gate. However, in order to drive top arm IGBTs, the gate voltage needs to be higher than the Vs voltage because the source voltage of top arm IGBTs rises near to Vs. For this operation, the driving by a floating power supply and the driving by a bootstrap system can be applied. ECN3053F can handle both types of driving.

(1) Driving by a floating power supply

Three floating power supplies of VFU, VFV, VFW are needed. Fig. 2 shows an example of a driving circuit for ECN3053F.

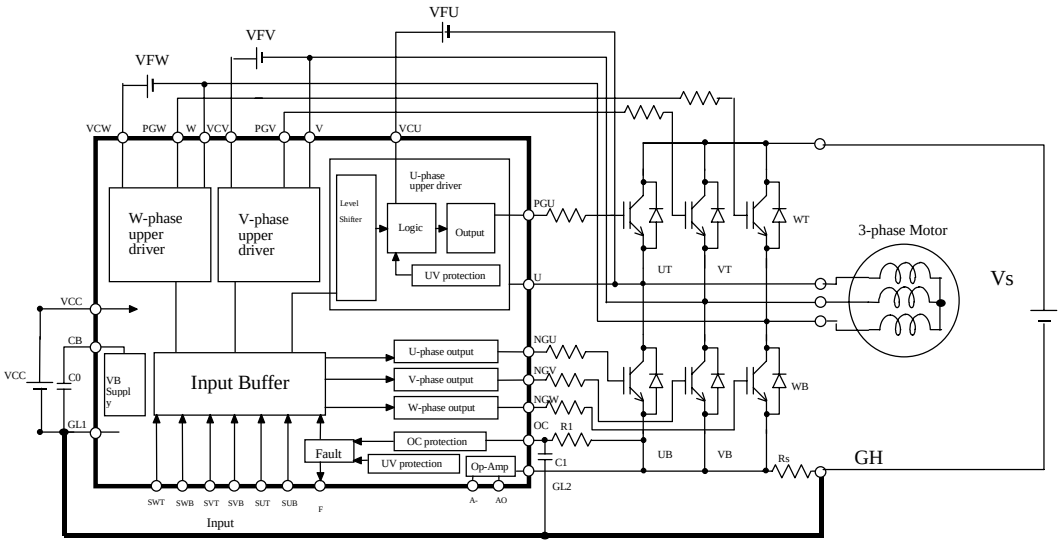



Fig. 2 Example of a driving by a floating power supply (for ECN3053F)

(2) Driving by a bootstrap system

Fig. 3 shows an example of a driving circuit using a bootstrap system. External capacitors Cb are used for a power supply to operate top arm driving circuits. One side of Cb is connected to the source of IGBTs to allow the driver circuit to have higher voltage than Vs.

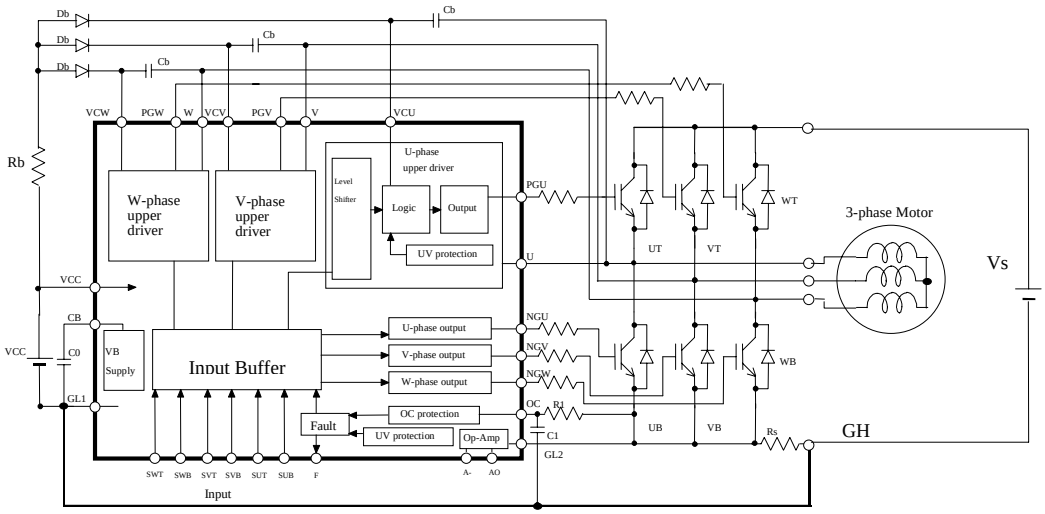



Fig. 3 Example of a driving by a bootstrap system (for ECN3053F)

Cb is charged by Vcc. The cost of a bootstrap drive is lower than that of a floating drive, however, a bootstrap drive needs to charge the capacitors for driving top arms at the beginning of the operation. And the maximum time for turning on top arm devices is limited by the value of Cb.

## 3. Internal block and functions

Using the example of a bootstrap drive in Fig. 3, internal functions are explained below.

(1) Input buffer

An ECN3053F package has a total of six input terminals : three top arm device inputs(each marked with a T) and three bottom arm device inputs(each marked with a B). SUB, SVB, SWB are U, V, W phase inputs for the bottom arm devices, respectively. SUT, SVT, SWT are U, V, W phase inputs for the top arm devices, respectively. Correspondence of these input terminals with output ones is shown in table 1. The six input terminals are pulled up by a

Table. 1 terminals and output terminals

| Arm | U-phase | V-phase | W-phase |
|---|---|---|---|
| Top | SUT: PGU | SVT: PGV | SWT: PGW |
| Bottom | SUB: NGU | SVB: NGV | SWB: NGW |

resistance(typ. 200k-ohm) in the internal circuit. Table 2 shows the pulled up

voltage. When ECN3053F is connected to a microprocessor directly, a pull up resistance RH is needed for 6 inputs terminals as shown in Fig. 4 in order to avoid a breakdown and a latch-up of output ports on a microprocessor. In Fig. 5, when the output signal of a microprocessor is low, current flows through RH.

Table 2. Pulled up voltage for input terminals

| type | Pulled up voltage |
|---|---|
| ECN3053F | Vcc |

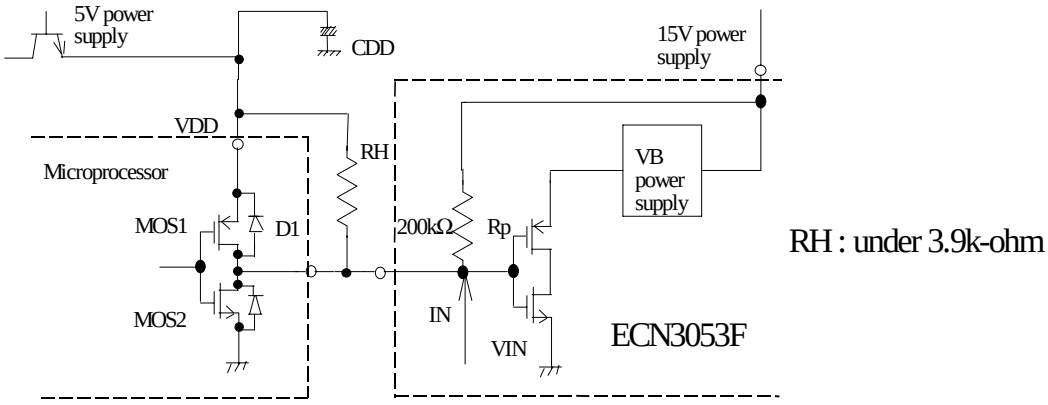



Fig. 4 Example for pulling up at a direct connection to a microprocessor

In ECN3053F, this current Is becomes more than 1mA. In order to avoid this, a resistance for dividing voltage can be used as shown in Fig. 5. For example, when R2 is 22k-ohm and R1 is 10k-ohm, Is becomes 0.68mA. The output signal of the IC is high when the input is low. Therefore, the external device is turned on when the input signal is low. The output device should be a device, like a n-channel IGBT, a n-channel MOSFET and so on, which can be turned on by a plus gate voltage against the source voltage.

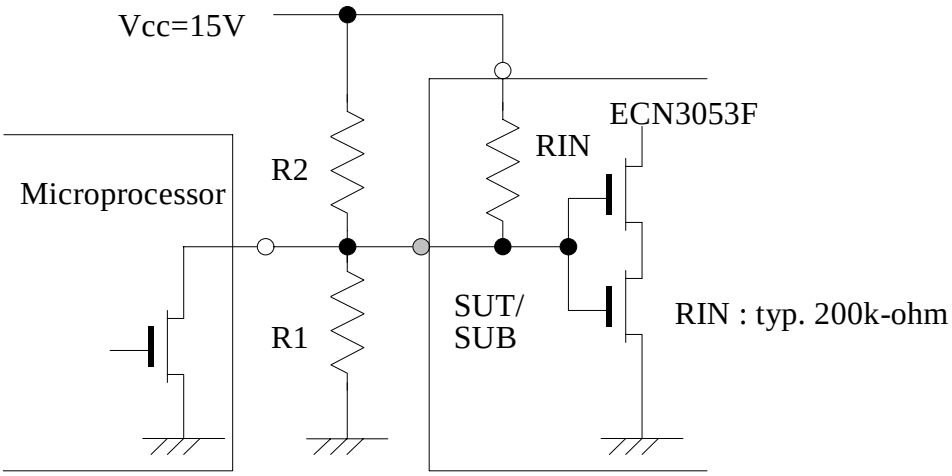



Fig 5. Configulation for R1 and R2

(2) Dead time

As shown in Fig. 2, the external devices at each phase are composed in such a way that the top and the bottom arm are built up like a totem pole. This makes it necessary to prevent the top and the bottom arm from turning on simultaneously at any instant when one arm(top or bottom) is switched on while the other arm(bottom or top) is on. In ECN3053F, on the other hand, a dead time is not generated internally. Therefore, a dead time must be set at the input signal side. The dead time must be at least double the sum of the ON/OFF delays of the internal and external output devices(except when such delays increase due to high temperature.)

(3) Level shift circuit

The top arm control circuit is operated under floating voltage of “output voltage of the external device + control voltage Vcc”. The level shift circuit converts input signals based on the ground level into top arm drive signals based on output voltages of each phase that constitute floating potentials. Inside the IC, a latch circuit is equipped with an edge trigger for top arm input signals in order to reduce the power consumption of the level shift circuit.

(4) Output section

The external output devices can be regarded as capacitive loads. Therefore, an IC

output circuit needs source and sink operation. ECN3053F incorporates a C-MOS type IC output. For both the top arm and the bottom arm, the value of the current ability is as follows,

Source current : 0.25A(typ.)

Sink current : 0.5A(typ.)

The amplitude of the bottom arm output voltage is nearly equal to Vcc, and the amplitude of the top arm output voltage is “the output voltage of the external devices(voltage at U, V, W terminal) + about Vcc”.

(5) Protective function

1)Bottom arm under voltage protection

When Vcc falls below the under voltage detection level(10.5V typ.) for bottom arms, the protective circuit turns off the output voltage of all the arms and sets the fault output terminal logic to L. When Vcc exceeds the under voltage detection level plus hysterisis voltage, the fault output signal is set to H again.

2)Over current protective function

When the input voltage of OC terminal exceeds a specified value for bottom arms(0.49V typ.), the protective circuit turns off the output voltages of all the arms and sets the fault output terminal logic to L. Until the reset is operated, the fault output is latched to L. The over current protection current setting level(IOC) is determined by the following equation,

IOC=VOC/RS (A) (Rs is an external resistance.)

Inside OC terminal which is the input for VOC signal, a filter of 0.4us is equipped. When over current protective function works by mistake due to some noise, an external filter with R1 and C1 should be added. Please see Fig. 8 for its configuration. Please be careful that the time to detect over current sense signal is delayed, if R1 and C1 are too large.

3)Top arm under voltage protective function

When any of the potentials VCU-U, VCV-V, and VCW-W falls below the under voltage level(10.5V typ.) for top arms, the protective circuit turns off the output voltage of the top arm of the corresponding phase only. In this case, the fault output remains unaffected.

4)Fault output terminal

This terminal is an open drain of n-MOS. Please pull it up via an external resistance Rf as follows. Rf should be more than 5.6k-ohm.

ECN3053F : to Vcc. CB or 5V

(Please refer to Fig. 6.)

When a opto-coupler is connected to this terminal, it should be connected between CB and Fault as shown in Fig. 7. The Fault output current should be 5mA(typ.) and a limiting resistance Rfc of 1k-ohm should be connected.

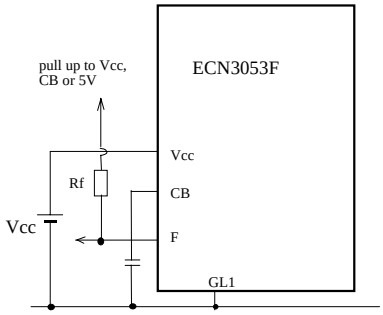



Fig. 6 Configulation for a pull up resistance to Fault

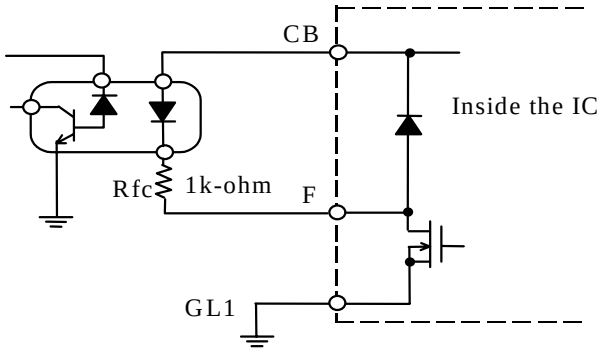



Fig 7. Configulation for a opto-coupler

To reset a fault output which has reached the L-level, please set all of the six input terminals of the top and the bottom arm to H. ( This reset can also be triggered by turning on the Vcc again.) Table 3 shows the truth table for reset input, OC, under voltage protective operation for bottom arms and Fault output.

Table 3. Truth table for Fault output

| Reset input | OC | Under voltage detection for bottom arms | Fault |
|---|---|---|---|
| 0 | 0 | 0 | H |
| 0 | 0 | 1 | L |
| 0 | 1 | 0 | L |
| 0 | 1 | 1 | L |
| 1 | 0 | 0 | H |
| 1 | 0 | 1 | L |
| 1 | 1 | 0 | L |
| 1 | 1 | 1 | L |

In this table, Reset input “1” shows that 6 input signals for top and bottom arms are H-level. OC “1” shows that over current protective operation works. Under voltage detection for bottom arms “1” shows that Under voltage protective operation for bottom arms works.

5)Operational amplifier

ECN3053F incorporate an operational amplifier designed to amplify current sense voltage. Before using the operational amplifier, please add an external gain resistance in line with the internal circuit shown in Fig. 8. If the operational amplifier need not be used, please connect A- to CB terminal in order to fix the output level of op-amp. In this case, the output of op-amp AO is 0V.

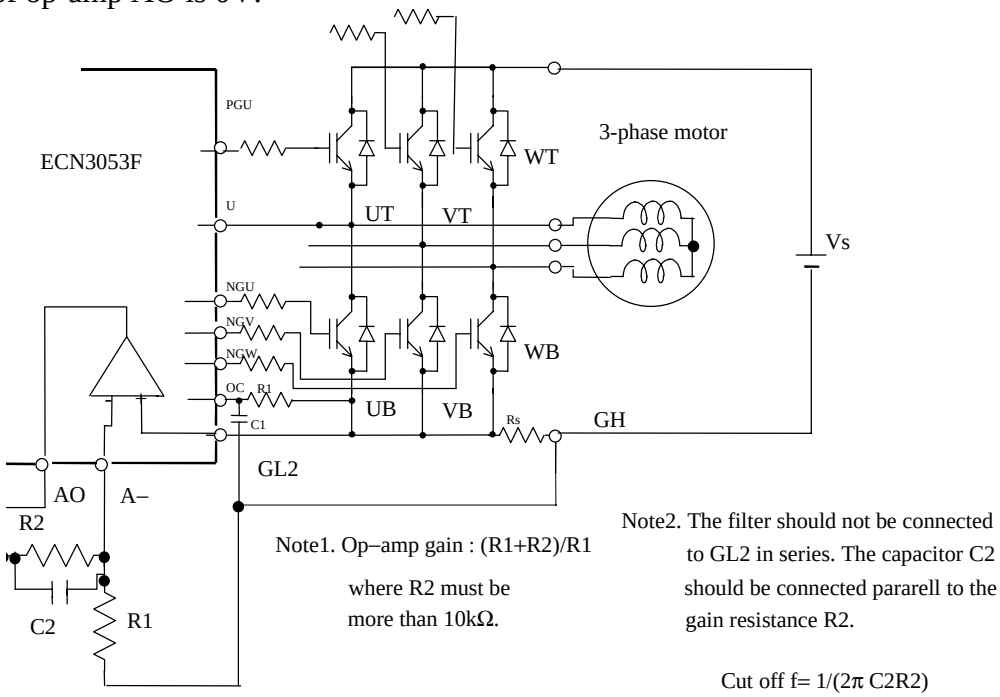


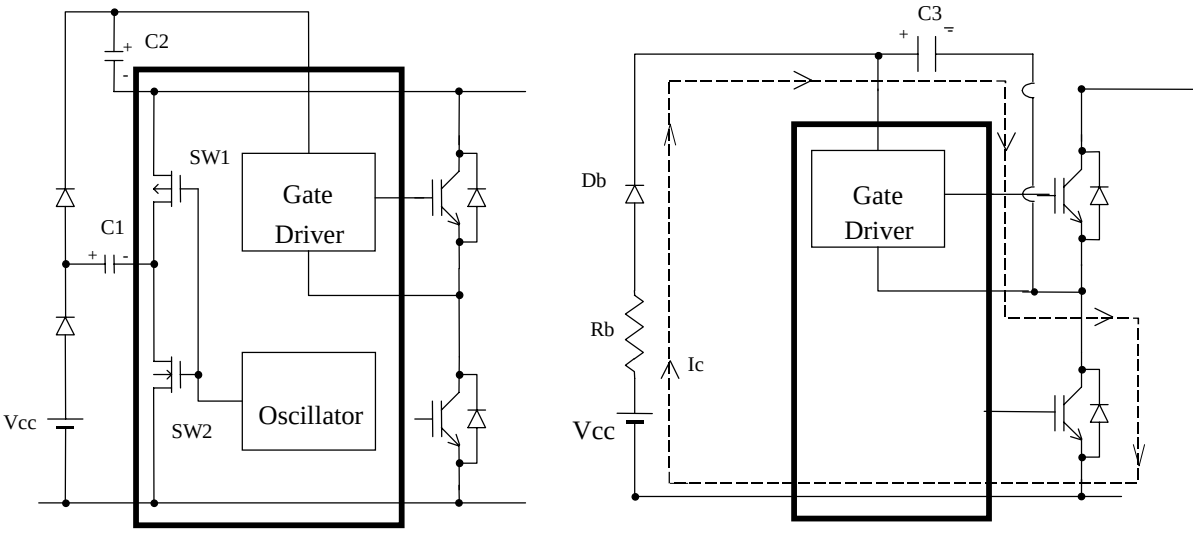

Fig. 8 Configulation for using an Op–amp

6)VB power supply

The input buffer, bottom arm protective circuit, fault logic circuit and others are operated by an internal power supply voltage VB≅8V generated by the VB power supply circuit using Vcc. CB terminal must be connected with an oscillation-preventive capacitor Co(0.22μF or more).

7)Bootstrap circuit

The top arm drive circuit is powered by a bootstrap circuit. The charge pump and the bootstrap system are briefly explained below. The charge pump system charges capacitors C1 and C2 while the switches inside the IC synchronize with the frequency of the internal oscillator regardless of the action of the output device. In Fig. 9(a), SW1 and SW2 are high-voltage devices but there are no limitations to the duty of the output device. In the bootstrap system shown in Fig. 9(b), C3 is charged when the switching device externally mounted on the bottom arm is turned on. The ON duty of the output device is therefore generally limited, but the gate driver inside the IC requires no high-voltage device. The ECN3053F can use this bootstrap system. And as listed in Item 2, a floating supply drive is also available. In this operation the duty of the top arm output device is not limited.




(a)Charge pump system (b)Bootstrap system

Fig. 9 Power supplying to a top arm circuit

## 4. Power consumption and temperature rising

(1) Power consumption

ECN3053F has three types of power consumption as below,

- Power dissipation for charging and discharging the gate capacitance of the external IGBTs or MOSFETs which are loads for the IC.
- Power dissipation for operating level shift circuit, etc. in the IC
- Power dissipation for charging and discharging parasitic capacitance inside the IC

The rate of power dissipation for the external devices is under 10% of all power dissipation. When Vcc is 15V, Vs is 280V and input capacitance for the IGBTs is 1000pF, the change of power dissipation with PWM frequency is shown in Fig. 10.

(2) Temperature rising

From Fig. 10, it can be seen that the power dissipation at a PWM frequency of 16kHz is 0.17W. For PLCC packages, the thermal resistance on the glass epoxy print board $R_{ja}$ is 70°C/W (print board size : 67×58.5×1.6mm, wire density 15%), therefore, temperature rise is 0.17×70=11.9°C.

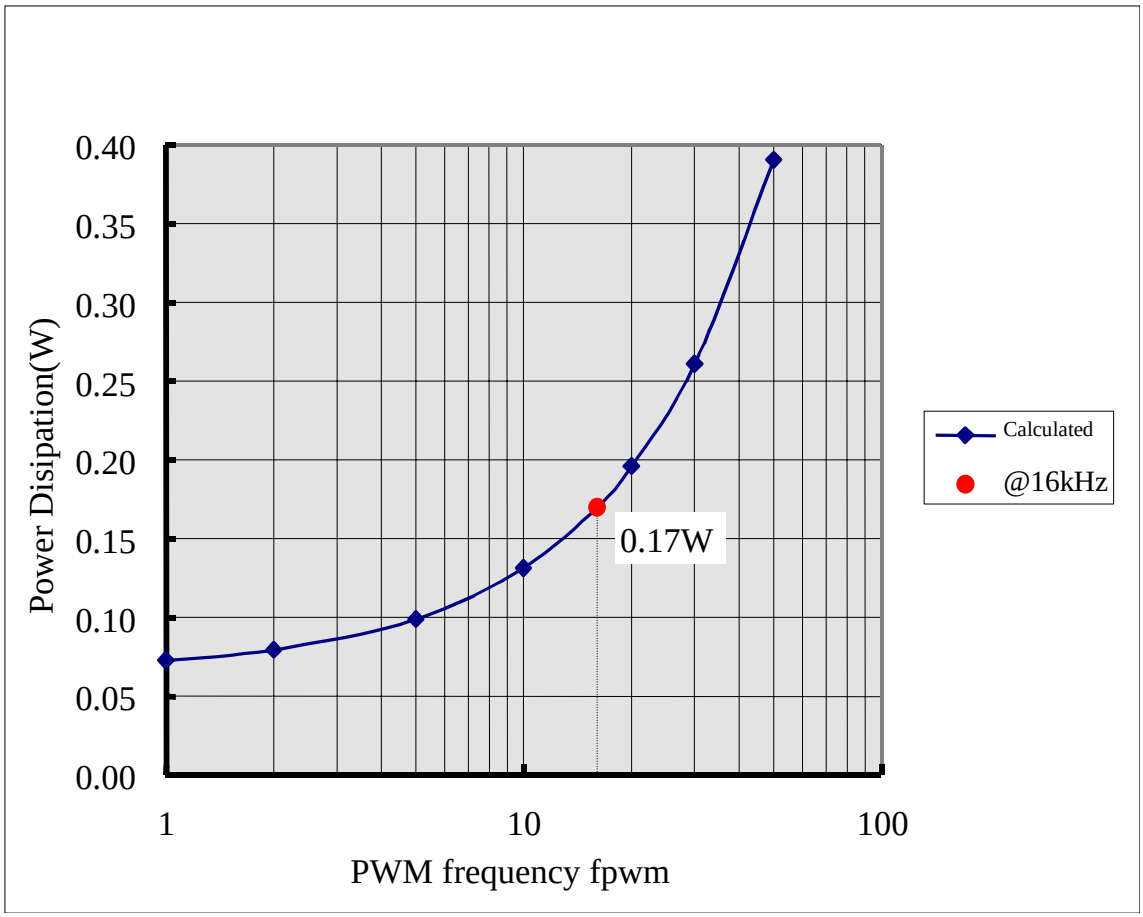



Fig. 10 Power dissipation with PWM frequency

## 5. Precautions

(1) Bootstrap capacitor : Cb, Current limiting resistance : Rb, Diode : Db

The capacitance of a bootstrap capacitor varies with switching frequency, the ON duty of an output device, and the gate capacitance of the external IGBTs or MOSFETs. A prolonged ON period of the top arm output device may lead to the top arm under voltage protective operation. For example, the longest ON time of the top arm output device is about 50ms when Cb is 3.3μF. Please refer to table 4 for calculated examples. Cb should be connected to the IC as near as possible in order to prevent the IC from getting destroyed by excess voltage. Current limiting resistance Rb should be added because the maximum charging current in Cb should be under the allowed value of the surge current for Db and over current protective operation should not work at the beginning of the charging Cb. Resistance Rb(in Fig. 9(b)) should be more than a few ohms. Diode Db needs more than 600V breakdown voltage, very small forward voltage drop and short reverse recovery time Trr of under 100ns.

[Approximate value of Cb and maximum on-time for top arms determined by the value of IGBTs]

If the bootstrap charge voltage is operated at -1V of GL2 and the forward voltage drop of diode Db is 1V, Cb is charged to 15V when Vcc is 15V. Now it is named Q1 that is needed to fully charge the gate of IGBTs or MOSFETs to 15V. When the leak current of top arms is 30μA, the time that the voltage of Cb decreases from 15V to 12V, that is the maximum value of under voltage detection voltage for top arms, is the maximum on-time of top arms Tonmax. Therefore, the following equation can be determined,

$$15\times Cb - Q1 - 30\mu A \times Tonmax = 12\times Cb$$

The value of Cb should be chosen from the maximum on-time for top arms and all the electric gate charge to drive the gate of IGBTs or MOSFETs. Table 4 shows the calculated examples.

Table 4 Calculated examples of Q1 and Tonmax

| Cb(μF) | Examples for output devices | Electric gate charge Q1(uC) | Maximum on-time for top arms Tonmax(ms) |
|---|---|---|---|
| 1.0 | 500V/10A MOS 2SK1516 | 0.036 | 99 |
| 1.0 | 600V/30A IGBT GN6030E | 0.085 | 97 |
| 3.3 | 600V/30A IGBT GN6030E | 0.085 | 327 |
| 5.6 | 600V/30A IGBT GN6030E | 0.085 | 557 |

The Cb of 3.3μF having some margin is recommended. However, it should be determined after confirmation by evaluation.

Recommended devices ;

Db : Hitachi DFG1C6 [600V/1A, Trr=100ns]

Cb : 3.3μF±20% [Stress voltage = 15V]

Rb : 3.3μF±20% [more than 2W]

(2)Output wiring

The output wiring that connects the output terminal of the ECN3053F to the external IGBTs or MOSFETs should be as short as possible in order to minimize the wire inductance. The frequency determined by the wiring inductance Lw and the gate capacitance Cg of the external devices oscillates the output wave form of the IC. When this oscillation voltage exceeds the maximum rating of the IC(for U-phase top arm output, for example, the PGU-U voltage is 20V, and for U-phase bottom arm output, NGU-GL1 voltage is 20V), the IC may get destroyed. Therefore, the following circuit elements should be connected near the top and the bottom arm output terminals of each phase of the IC as shown in Fig. 11.

Capacitance CP = 560μF (If the wiring is about 30cm long, the value should be adjusted according to the wiring length. A ceramic capacitance should be used.)

Resistor Rg(in series with the gate) = 100 ohms (If an external IGBT of 20A or so is used, this value increases as the current rating of the external device decreases.)

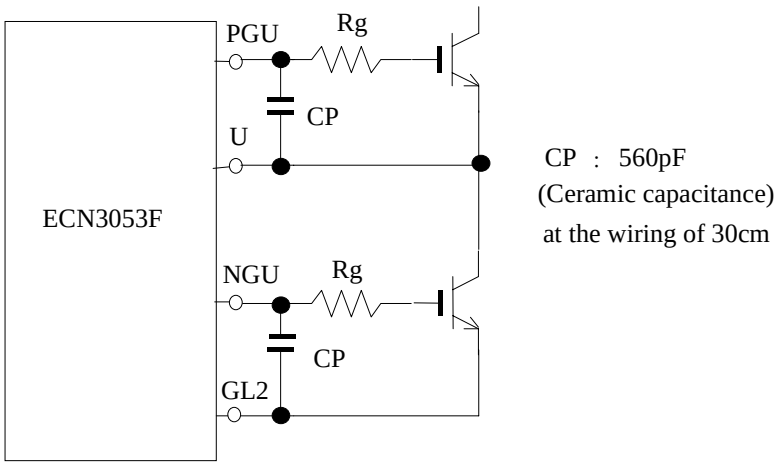
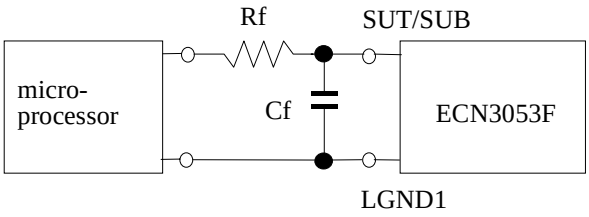



Fig. 11 Adding an oscillation-preventive capacitance (this figure shows the case of the U-phase alone)

(3)Caution for noise at input terminals

6 input terminals tend to have an influence of switching noise from the external terminals because the input impedance is large. Therefore, when designing a print board, it should be careful that switching noise of external terminals should not affect the input terminals. When it is evaluated by a temporally wiring, the filters shown in Fig. 12 should be connected to 6 input terminals. In this case, please confirm that the arm short circuit of the external devices does not occur because of the input pulse delay.




Rf=10kΩ, Cf=100~560pF

Fig.12 Adding filters for input terminals

(4)Setting the bottom arm device input for bootstrap initial charge

Top arm drive circuits use the bootstrap system. Therefore, the top arm output device can not be turned on unless the bootstrap capacitance Cb is charged to about 11V or more. When the power supply is turned on, the capacitance Cb is considered to be 0V in initial voltage. The Cb can be charged by turning on the bottom arm of the corresponding phase. The on-

time of the reset for the bottom arm can be determined from the impedance, Rb and Cb of the charging circuit marked with a broken line in Fig. 9(b). Generally, for the initial charge after turning on the power supply, the pulse width of three times as large as T=Rb×Cb for the bottom arm-on should be input, or more than 3 on-pulses of T=Rb×Cb for the bottom arm should be input.

(5)Using external drive devices having a large capacitance

Connecting a C-MOS buffer to the IC output may allow IGBTs or MOSFETs of more than 30A to be driven. In this case, the quick switching of the output large-current device causes spike voltage or oscillation, which may result in the IC malfunctioning or the device getting destroyed. When driving IGBTs or MOSFETs of more than 30A, please consult Hitachi about it.

(6)Separating the high- and low-voltage ground wiring

In the block diagram and the external elements shown in Fig. 2, 3, PWM voltage and current flows through the high-voltage ground wiring at controlling motors because Vs power supply deals with high-voltage and high-current. This high-voltage and high-current should not be flown through the ground wiring of Vcc which deals with low-voltage and low-current. Therefore, these ground wirings should be connected separately on the print board and should be provided with common line near the power supply. (marked with the thick line connecting GL1 and GH at the bottom of Fig. 2 and Fig. 3)

(7)Adding a capacitor for a power supply between Vcc and GL1

The noise voltage caused by L×di/dt of the wiring inductance may be produced at Vcc terminal of the IC and exceeds the maximum voltage, and may get destroyed. Therefore, a chemical capacitor should be connected near Vcc terminal of the IC. The value of this capacitance should be more than 10 times as large as the bootstrap capacitor Cb.

(8)Caution for no connection terminals

All the no connection(N.C.) terminals are not used for the connection inside the IC. However, they are parts of the parasitic capacitance for this IC due to the operation for this IC. Therefore, when wiring is connected to a N.C terminal on a print board, please consult Hitachi about it.

# HITACHI POWER SEMICONDUCTORS

## Notices

1. The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are adviced to contact Hitachi sales department for the latest version of this data sheets.
2. Please be sure to read "Precautions for Safe Use and Notices" in the individual brochure before use.
3. In cases where extremely high reliability is required(such as use in nuclear power control, aerospace and aviation, traffic equipment, life-support-related medical equipment, fuel control equipment and various kinds of safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement. Or consult Hitachi's sales department staff.
4. In no event shall Hitachi be liable for any damages that may result from an accident or any other cause during operation of the user's units according to this data sheets. Hitachi assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in this data sheets.
5. In no event shall Hitachi be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
6. No license is granted by this data sheets under any patents or other rights of any third party or Hitachi, Ltd.
7. This data sheets may not be reproduced or duplicated, in any form, in whole or in part , without the expressed written permission of Hitachi, Ltd.
8. The products (technologies) described in this data sheets are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety not are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.

■ For inquiries relating to the products, please contact nearest overseas representatives which is located "Inquiry" portion on the top page of a home page.

Hitachi power semiconductor home page address http://www.hitachi.co.jp/pse

HITACHI